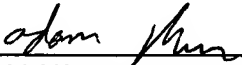
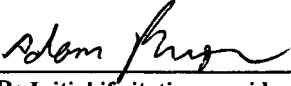


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EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
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	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO	
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